

N-Channel Enhancement Mode MOSFET

Description

The NTTFS015N04C-HXY uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

 $V_{DS} = 40V I_{D} = 50A$

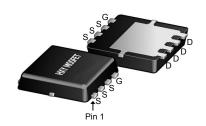
 $R_{DS(ON)} < 14m\Omega$ $V_{GS}=10V$

Application

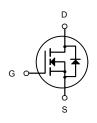
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
NTTFS015N04C-HXY	DFN5X6-8L	50N04 XXX YYYY	5000

Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	40	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	50	Α
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	38	Α
Ірм	Pulsed Drain Current ²	160	Α
EAS	Single Pulse Avalanche Energy ³	50	mJ
Тѕтс	Storage Temperature Range	-55 to 175	°C
TJ	Operating Junction Temperature Range	-55 to 175	°C

NTTFS015N04C-HXY

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Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	$R_{ heta JC}$	1.76	°C/W	
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Off Characteristics			1			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	·		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)		1	1			1
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	11	14	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	30	-	-	S
Dynamic Characteristics (Note4)			1			
Input Capacitance	C _{Iss}	V 05)/// 0)/	-	1540	-	PF
Output Capacitance	C _{oss}	$V_{DS}=25V, V_{GS}=0V,$	-	171	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	115	-	PF
Switching Characteristics (Note 4)			1			1
Turn-on Delay Time	t _{d(on)}		-	5.0	-	nS
Turn-on Rise Time	t _r	$V_{DD}=20V,I_{D}=20A,R=1\Omega$	-	24	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	38	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	\/ 00\/I 00A	-	24	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=30A,$	-	5.9	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.6	-	nC
Drain-Source Diode Characteristics			1			1
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	48	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =30A	-	9		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	15		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

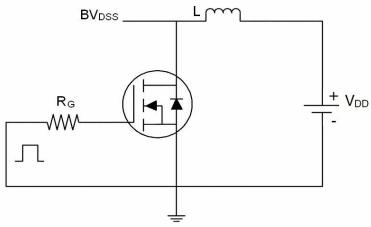
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25 Ω

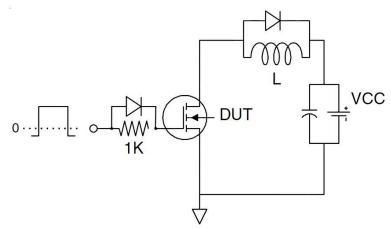
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Test circuit

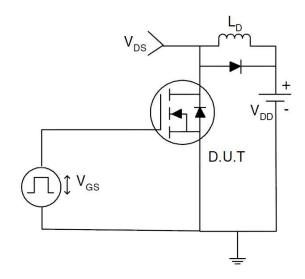
1) E_{AS} test Circuits



2) Gate charge test Circuit

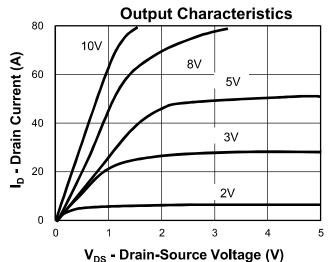


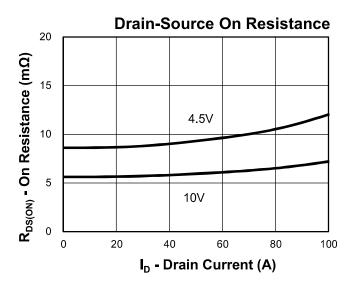
3) Switch Time Test Circuit

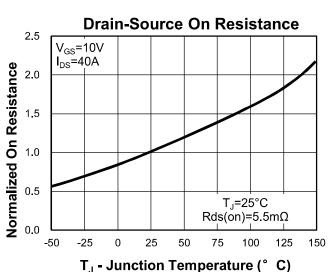


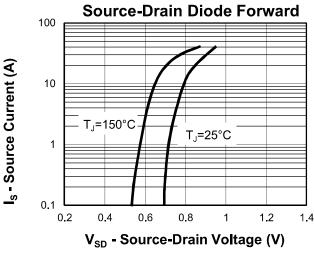


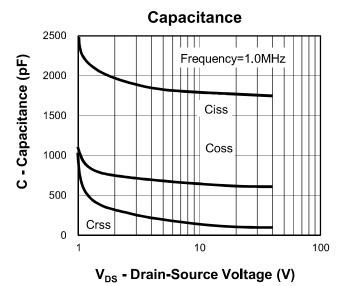
Typical Characteristics

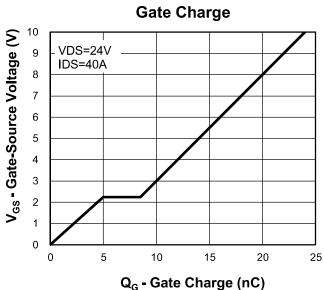






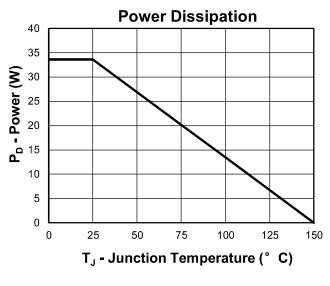


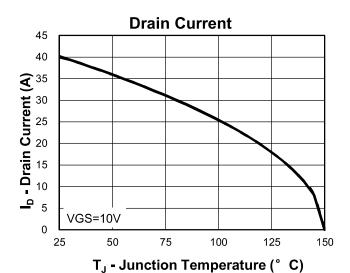


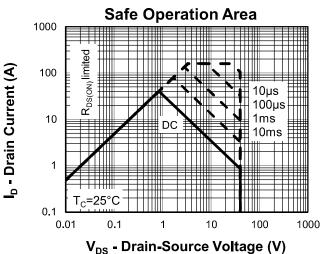


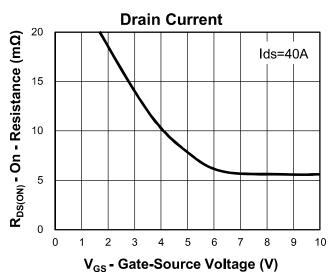


Typical Characteristics

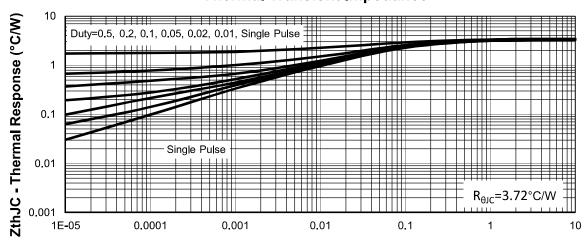








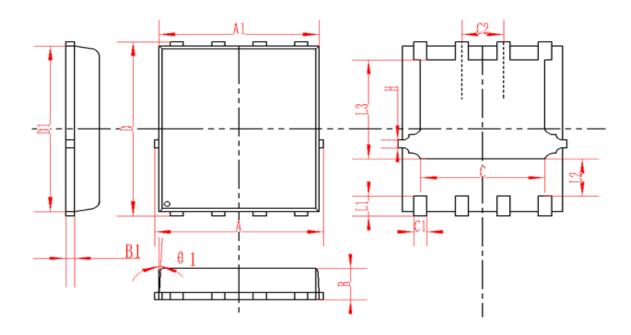
Thermal Transient Impedance



Square Wave Pulse Duration (sec)

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DFN5X6-8L Package Information



SYMBOL	MM			INCH		
STIVIDOL	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Η	0.24	0.25	0.26	0.009	0.010	0.010



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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
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DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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